



SEMITRANS® 4

Trench IGBT Modules

SKM 600GA176D

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications*

- AC inverter drives mains 575 - 790 V AC
- Public transport (auxiliary systems)

Remarks

- $I_{DC} \leq 500$ A limited for $T_{Terminal} = 100^\circ\text{C}$

Absolute Maximum Ratings		T _{case} = 25°C, unless otherwise specified		
Symbol	Conditions		Values	Units
IGBT				
V _{CES}	T _j = 25 °C		1700	V
I _C	T _j = 150 °C	T _c = 25 °C	660	A
		T _c = 80 °C	470	A
I _{CRM}	I _{CRM} =2xI _{Cnom}		800	A
V _{GES}			± 20	V
t _{psc}	V _{CC} = 1200 V; V _{GE} ≤ 20 V; T _j = 125 °C V _{CES} < 1700 V		10	μs
Inverse Diode				
I _F	T _j = 150 °C	T _c = 25 °C	600	A
		T _c = 80 °C	410	A
I _{FRM}	I _{FRM} =2xI _{Fnom}		800	A
I _{FSM}	t _p = 10 ms; sin.	T _j = 150 °C	3800	A
Module				
I _{t(RMS)}			500	A
T _{vj}			- 40 ... +150	°C
T _{stg}			- 40 ... +125	°C
V _{isol}	AC, 1 min.		4000	V

Characteristics			T _{case} = 25°C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 16 mA		5,2	5,8	6,4	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C		4			mA
V _{CE0}	T _j = 25 °C		1			V
	T _j = 125 °C		0,9			V
r _{CE}	V _{GE} = 15 V T _j = 25°C		2,5			mΩ
	T _j = 125°C		3,9			mΩ
V _{CE(sat)}	I _{Cnom} = 400 A, V _{GE} = 15 V T _j = 25°C _{chiplev.}		2			V
	T _j = 125°C _{chiplev.}		2,45			V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz		28,4			nF
C _{oes}			1,46			nF
C _{res}			1,17			nF
t _{d(on)}	R _{Gon} = 3 Ω	V _{CC} = 1200V I _C = 400A	290			ns
t _r			70			ns
E _{on}	R _{Goff} = 3 Ω	T _j = 125 °C V _{GE} = ±15V	255			mJ
t _{d(off)}			890			ns
t _f			160			ns
E _{off}			155			mJ
R _{th(j-c)}	per IGBT		0,044			K/W



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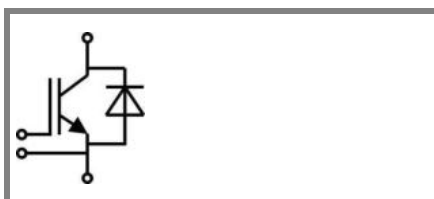
Remarks

- $I_{DC} \leq 500$ A limited for $T_{Terminal} = 100^\circ\text{C}$

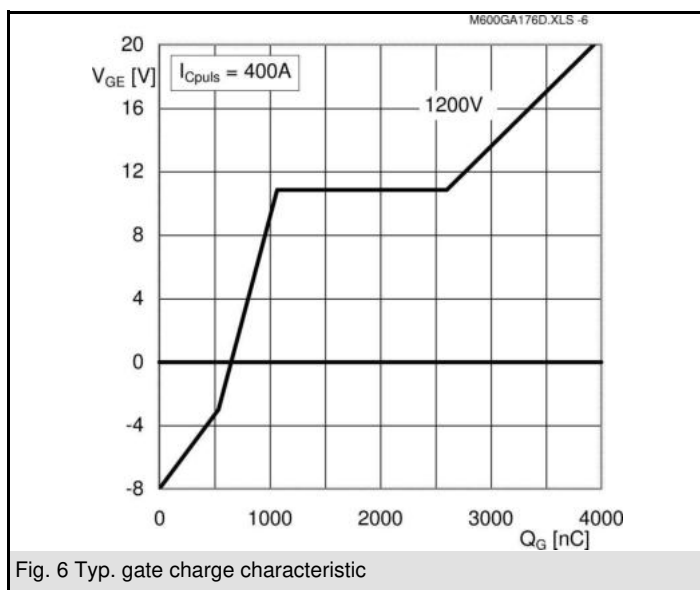
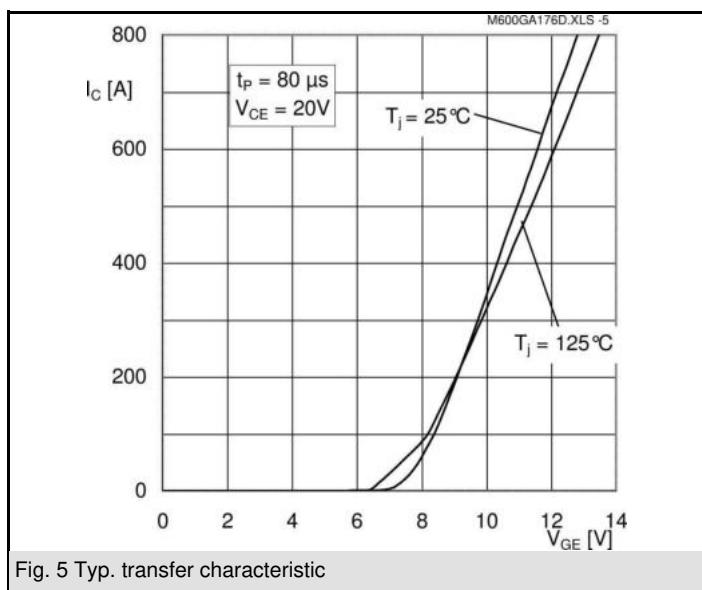
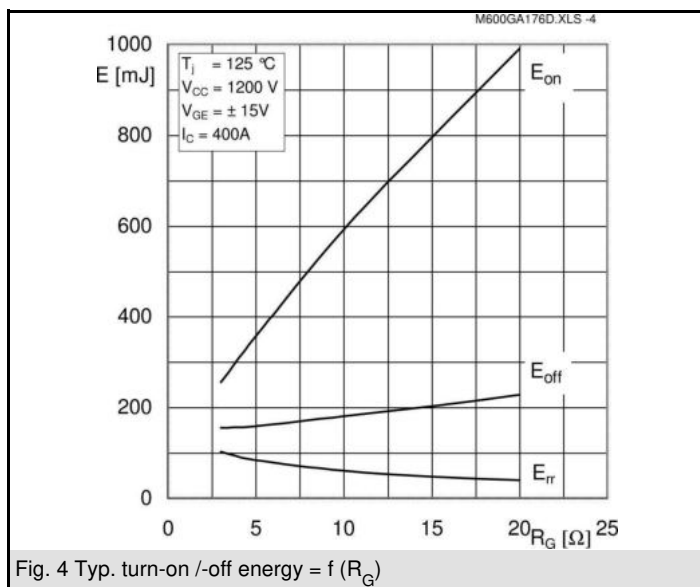
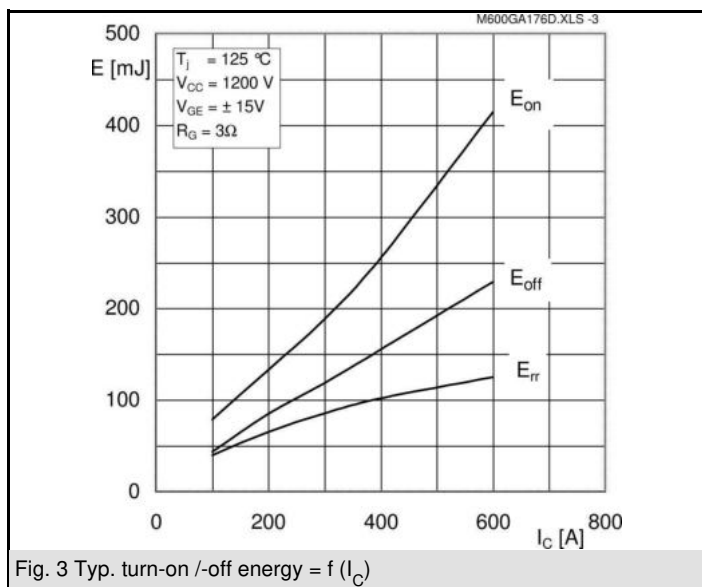
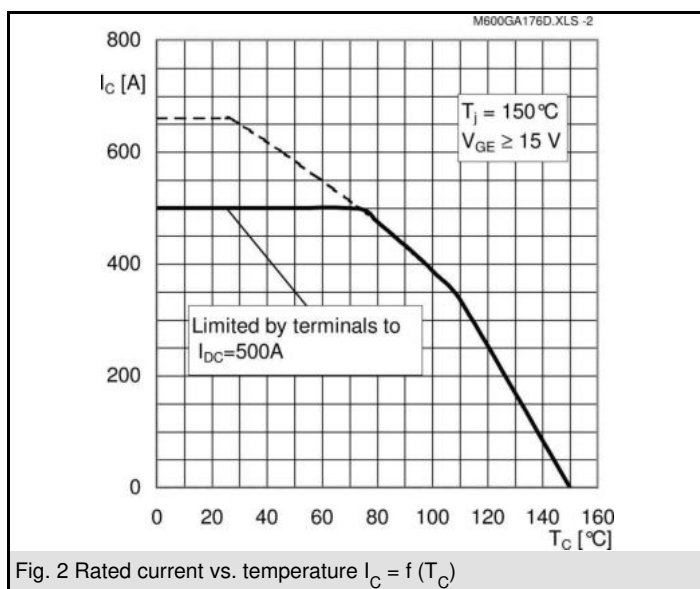
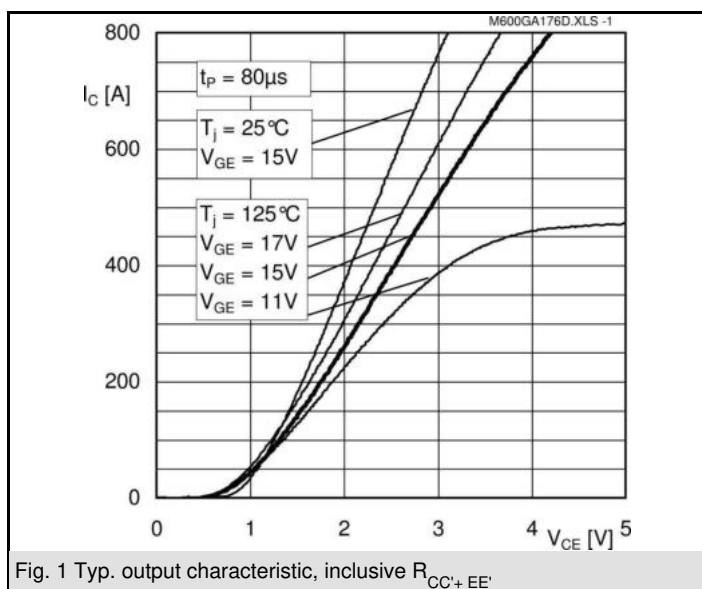
Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 400$ A; $V_{GE} = 0$ V				
	$T_j = 25^\circ\text{C}_{chiplev.}$		1,6	1,9	V
	$T_j = 125^\circ\text{C}_{chiplev.}$		1,6	1,9	V
V_{F0}	$T_j = 25^\circ\text{C}$		1,1	1,3	V
r_F	$T_j = 25^\circ\text{C}$		1,3	1,5	mΩ
I_{RRM}	$I_F = 400$ A		510		A
Q_{rr}	$di/dt = 5700$ A/μs		155		μC
E_{rr}	$V_{GE} = -15$ V; $V_{CC} = 1200$ V		102		mJ
$R_{th(j-c)D}$	per diode			0,09	K/W
Module					
L_{CE}			15	20	nH
$R_{CC'+EE'}$	res., terminal-chip		0,18		mΩ
	$T_{case} = 25^\circ\text{C}$		0,22		mΩ
	$T_{case} = 125^\circ\text{C}$				
$R_{th(c-s)}$	per module			0,038	K/W
M_s	to heat sink M6	3		5	Nm
M_t	to terminals M6 (M4)	2,5 (1,1)		5 (2)	Nm
w				330	g

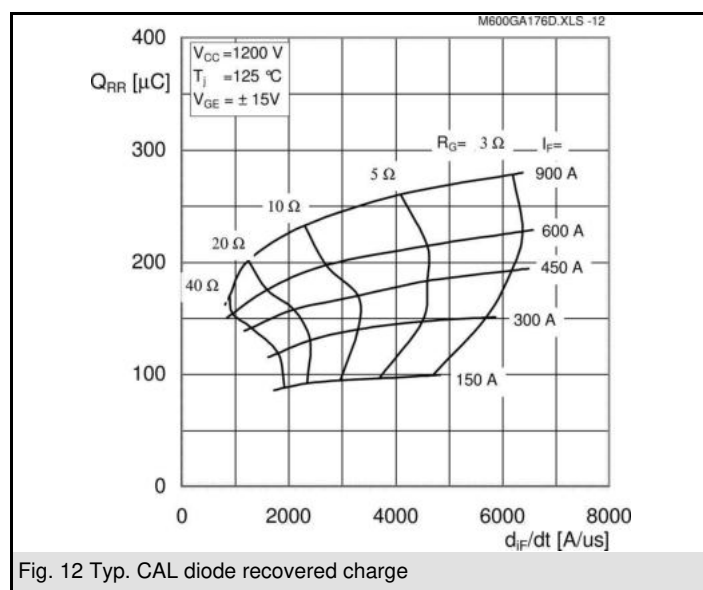
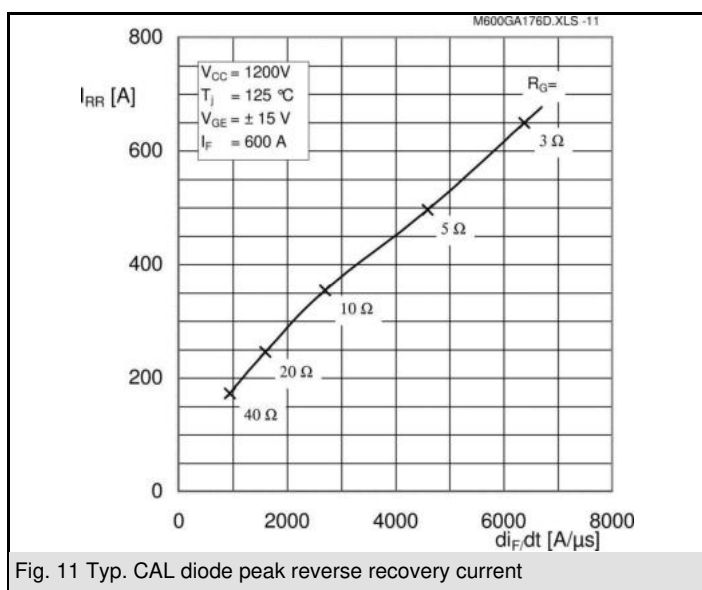
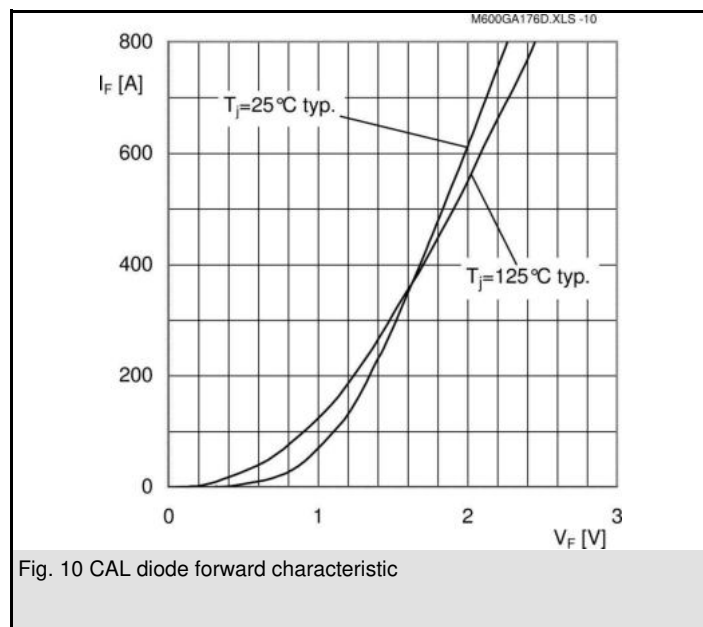
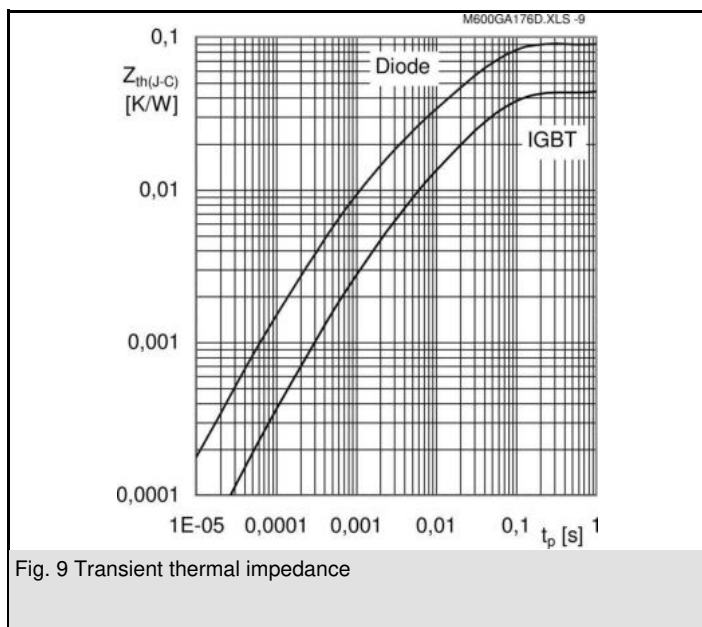
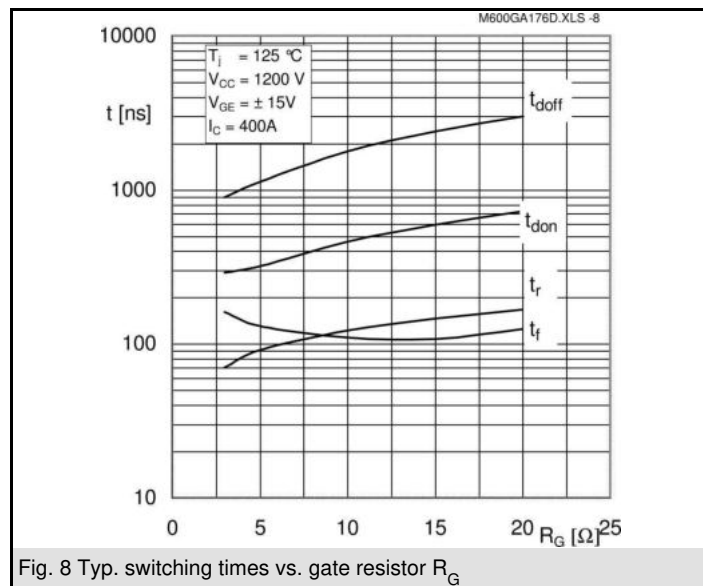
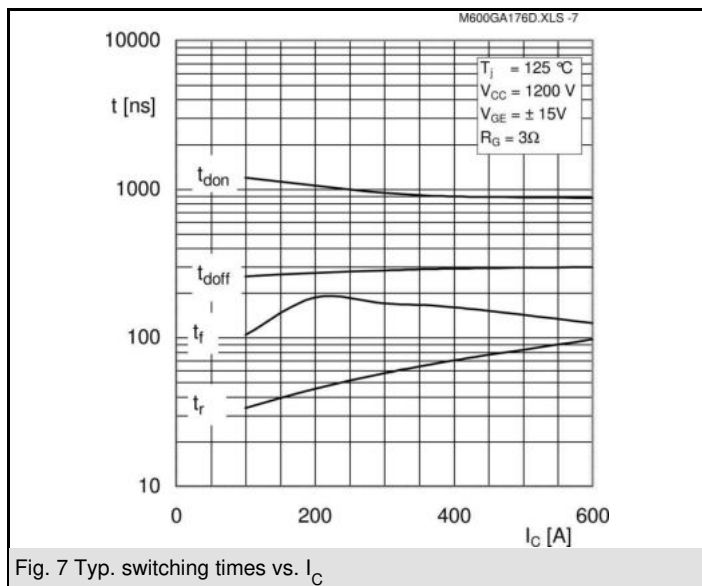
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



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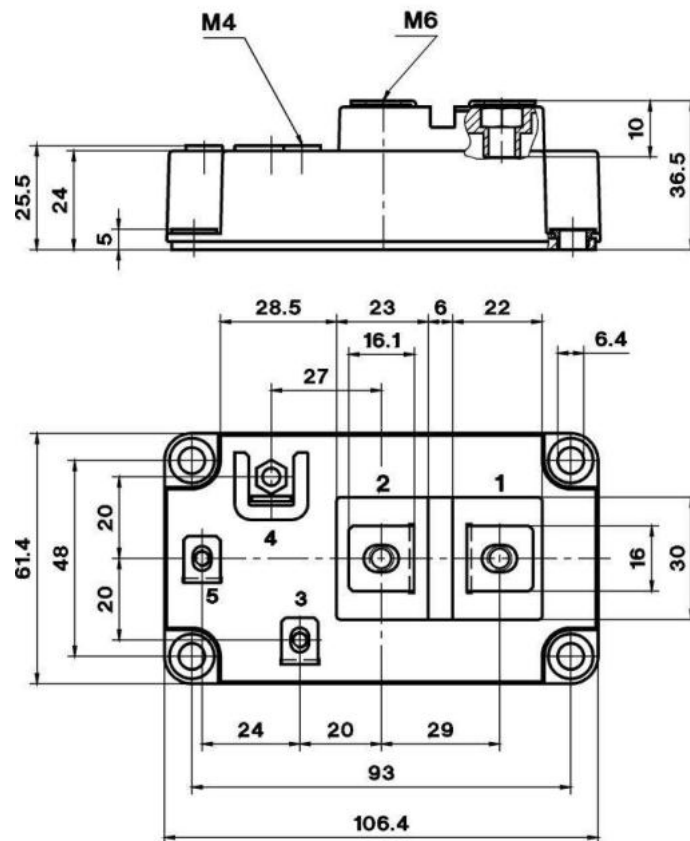




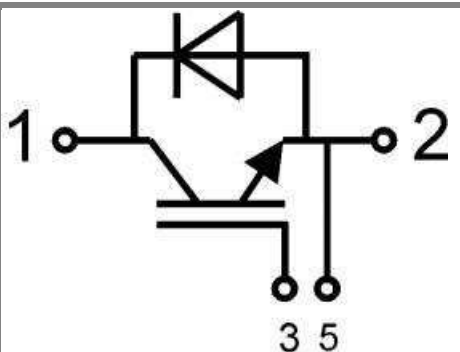
UL Recognized

CASED59

File no. 63 532



Case D 59



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Case D59